

MOSFETs Silicon N-channel MOS (U-MOS11-H)

TPHR6704RL

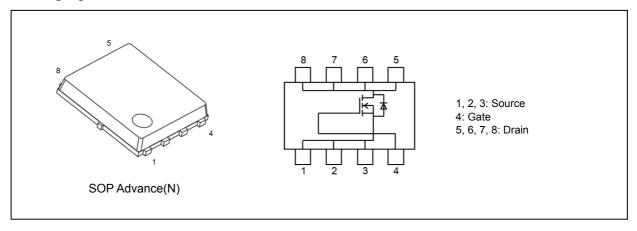
1. Applications

- High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 24 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 100 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 0.52 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 1.0$ to 2.0 V ($V_{DS} = 10$ V, $I_D = 1.0$ mA)

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics	3		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	40	V
Gate-source voltage		(Note 1)	V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 2), (Note 3)	I _D	420	Α
Drain current (DC)		(Note 2), (Note 4)	I_D	50	Α
Drain current (pulsed)	(t = 100 μs)	(Note 2)	I_{DP}	500	Α
Power dissipation	(T _c = 25 °C)		P_D	210	W
Power dissipation		(Note 4)	P_{D}	3.0	W
Power dissipation		(Note 5)	P_{D}	0.96	W
Single-pulse avalanche energy		(Note 6)	E _{AS}	457	mJ
Single-pulse avalanche current		(Note 6)	I _{AS}	75	Α
Channel temperature			T _{ch}	175	ů
Storage temperature			T _{stg}	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: In this product, radiation resistance and cosmic ray resistance are not designed, and these natural environmental factors may affect reliability.

In addition, radiation from the constituent materials of the product also becomes a natural environmental factor which may affect reliability.

5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	0.71	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	50	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 5)	R _{th(ch-a)}	156	

Note 1: +20V /-16V ensured at DC condition.

-20V ensured at pulse condition(duty 10%)

Note 2: Ensure that the channel temperature does not exceed 175 °C.

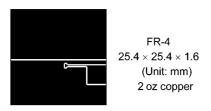
Note 3: This is the maximum rated current when the case temperature is maintained at 25°C.

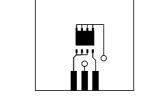
The case temperature indicates the entire bottom side.

Note 4: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 5: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 6: V_{DD} = 20 V, T_{ch} = 25 °C (initial), L = 100 μ H, I_{AS} = 75 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	40			V
Drain-source breakdown voltage (Note 7)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	25	_	_	
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1.0 mA	1.0	_	2.0	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = 4.5 \text{ V}, I_D = 60 \text{ A}$	_	0.75	0.97	mΩ
		V _{GS} = 10 V, I _D = 75 A	_	0.52	0.67	

Note 7: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	_	5990	9000	pF
Reverse transfer capacitance	C _{rss}		_	85	180	
Output capacitance	C _{oss}		_	2080	_	
Gate resistance	r _g	_	_	0.8	1.3	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	110	_	ns
Switching time (turn-on time)	t _{on}		_	120	_	
Switching time (fall time)	t _f		_	44	_	
Switching time (turn-off time)	t _{off}		_	120	_	

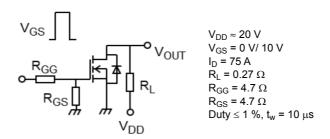


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	_	88	_	nC
gate-drain)		$V_{DD} \approx 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 60 \text{ A}$		43	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	_	19	_	
Gate-drain charge	Q_{gd}		_	13.2	_	
Gate switch charge	Q_SW		_	24	_	
Output charge	Q _{oss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	_	100	_	



6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 8)	I _{DRP} (t = 100 μs)		1	ı	500	Α
Diode forward voltage	V_{DSF}	I _{DR} = 75 A, V _{GS} = 0 V			-1.2	V
Reverse recovery time		V _R = 20 V, I _{DR} = 75 A, V _{GS} = 0	_	73	_	ns
Reverse recovery charge	Q _{rr}	V, -dI _{DR} /dt = 100 A/μs		106	_	nC

Note 8: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

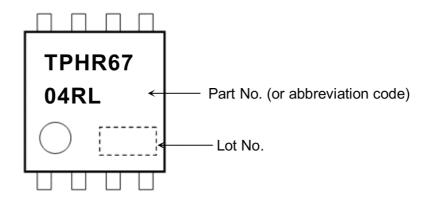


Fig. 7.1 Marking



8. Characteristics Curves (Note)

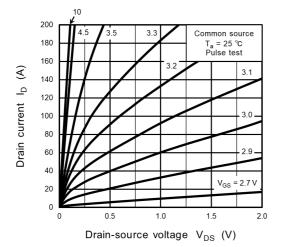


Fig. 8.1 I_D - V_{DS}

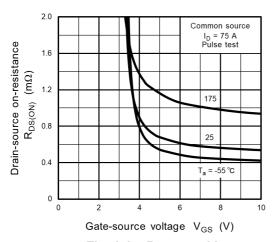


Fig. 8.3 R_{DS(ON)} - V_{GS}

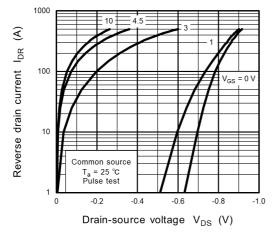


Fig. 8.5 I_D - V_{DS}

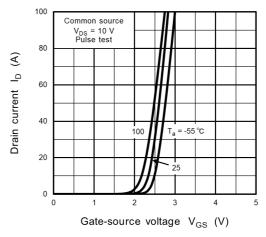


Fig. 8.2 ID - VGS

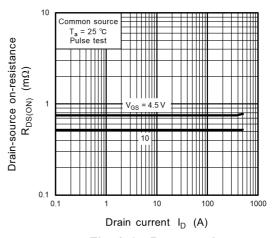


Fig. 8.4 R_{DS(ON)} - I_D

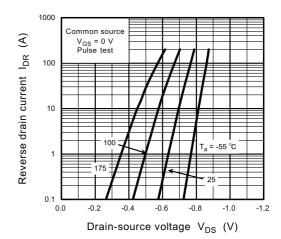


Fig. 8.6 IDR - VDS



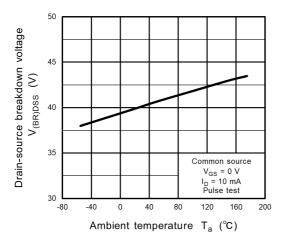


Fig. 8.7 V_{(BR)DSS} - T_a

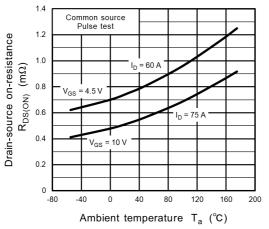


Fig. 8.9 R_{DS(ON)} - T_a

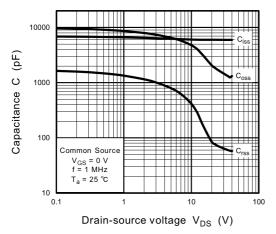


Fig. 8.11 Capacitance - V_{DS}

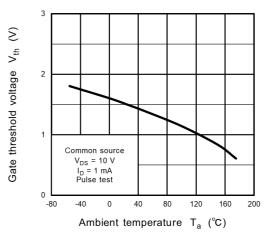


Fig. 8.8 V_{th} - T_a

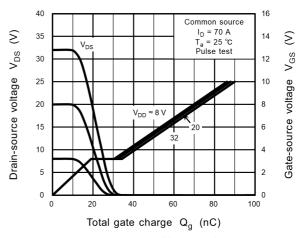


Fig. 8.10 Dynamic Input/Output Characteristics

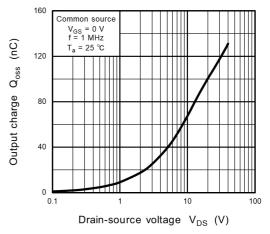


Fig. 8.12 Qoss - VDS



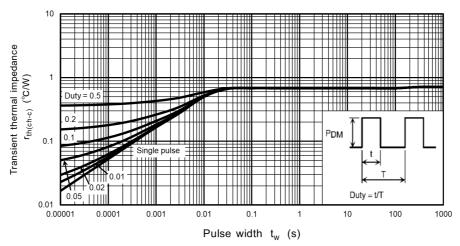


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

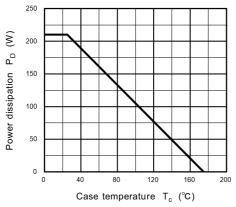


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

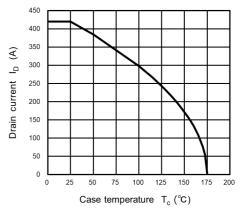


Fig. 8.15 I_D - T_c

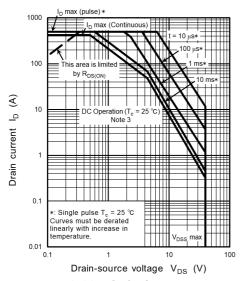


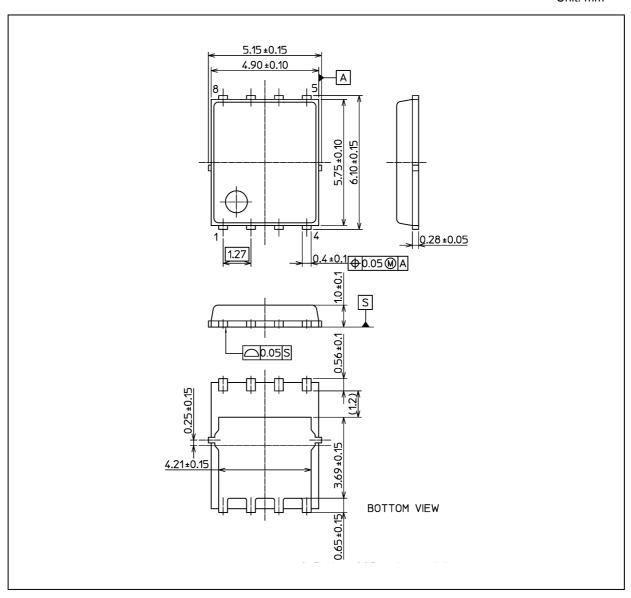
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.111 g (typ.)

Package Name(s)
TOSHIBA: 2-5W1A
Nickname: SOP Advance(N)



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